TGM2635-CP X-Band 100 W GaN Power Amplifier

Product Overview

Qorvo's TGM2635–CP is a packaged X-band, high power amplifier fabricated on Qorvo's production 0.25um GaN on SiC process. The TGM2635–CP operates from 7.9-11GHz and provides 100 W of saturated output power with 22.5 dB of large signal gain and greater than 35 % power– added efficiency.

The TGM2635-CP is packaged in a 10-lead 19.05 x 19.05 mm bolt-down package with a pure Cu base for superior thermal management. Both RF ports are internally DC blocked and matched to 50 ohms allowing for simple system integration.

The TGM2635-CP is ideally suited for both commercial and military X-Band radar systems, satellite communications systems, and data links.

RoHS compliant.



Key Features

- Frequency Range: 7.9 11 GHz
- P_{SAT}: 50 dBm (P_{IN} = 28 dBm)
- PAE: 35% (P_{IN} = 28 dBm)
- Large Signal Gain: 22 dB (P_{IN} = 28 dBm)
- Small Signal Gain: 26 dB
- Bias: V_D = 28 V, I_{DQ} = 1.3 A
- Package Dimensions: 19.05 x 19.05 x 4.52 mm
- Performance Under Pulsed Operation

Functional Block Diagram



Applications

- X-band Radar
- Satellite Communications
- Data Links

Ordering Information

Part	Description		
TGM2635-CP	X-band 100 W GaN Power Amplifier		

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Absolute Maximum Ratings

Parameter	Rating
Drain Voltage (V _D)	40 V
Gate Voltage Range (V _G)	−8 to −0 V
Drain Current (I _D)	16 A
Gate Current (I _G)	See plot page 9
Power Dissipation (P _{DISS}), 85°C, Pulsed; PW = 100 us, DC = 10%	316 W
Input Power (P _{IN}), 50 Ω , 85°C , VD = 28 V, Pulsed; PW = 100 us, DC = 10%	33 dBm
Input Power (PI _N), 85°C, VSWR 3:1, VD = 28 V, Pulsed; PW = 100 us, DC = 10%	33 dBm
Mounting Temperature	Refer to Assembly Notes, page 13
Storage Temperature	−55 to 150 °C

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability.

Recommended Operating Conditions

Parameter	Value/Range		
Drain Voltage (V _D)	28 V		
Drain Current (I _{DQ} , total)	1.3 A		
Drain Current (Under drive, ID_TOTAL)	See plots pg. 3-5		
Operating Temperature Range	−40 to +85 °C		

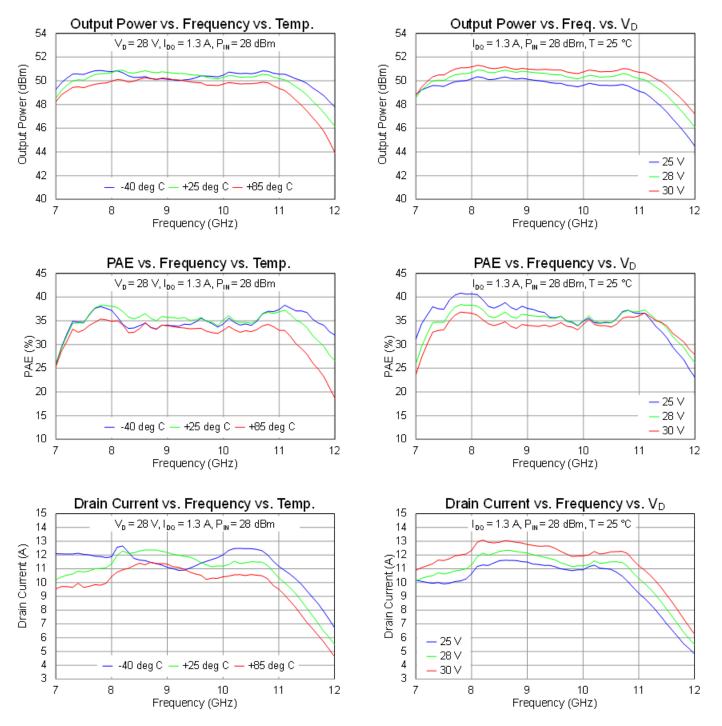
Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications

Parameter	Conditions ⁽¹⁾	Min	Тур	Max	Units
Frequency Range		7.9		11.0	GHz
	P _{IN} = 28 dBm, Pulsed				
	8 GHz	50.0	51.0		
Output Power	9 GHz	50.0	51.0		dBm
	10 GHz	49.5	51.0		
	11 GHz	49.5	51.0		
	P _{IN} = 28 dBm, Pulsed				
	8 GHz	37	41		
Power Added Efficiency	9 GHz	33	41		%
	10 GHz	35	41		
	11 GHz	33	41		
Power Gain	P _{IN} = 28 dBm, Pulsed		23		dB
Output Power Temperature Coefficient Temp: 25 °C to 85 °C, P _{IN} = 28 dBm)			-0.010		dB/°C
Input Return Loss			12		dB
Output Return Loss			12		dB
Small Signal Gain			26		dB
Recommended Operating Voltage		20	28	30	V
Gate Leakage Current $V_D = =10 V, V_G = -3.7 V$		-58.1			mA

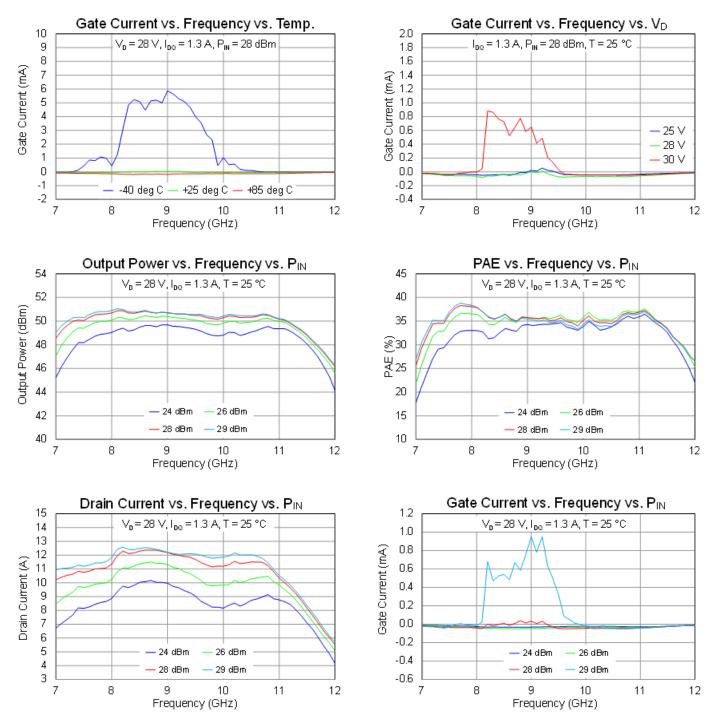
TGM2635-CP X-Band 100 W GaN Power Amplifier

Performance Plots – Large Signal (Pulsed)



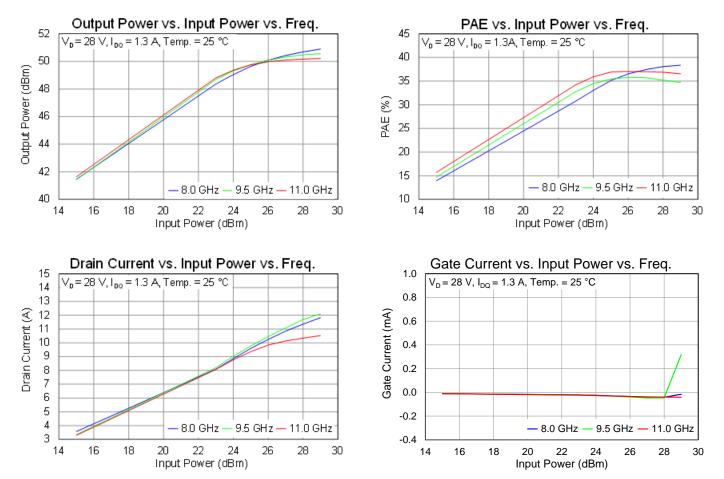
TGM2635-CP X-Band 100 W GaN Power Amplifier

Performance Plots – Large Signal (Pulsed)



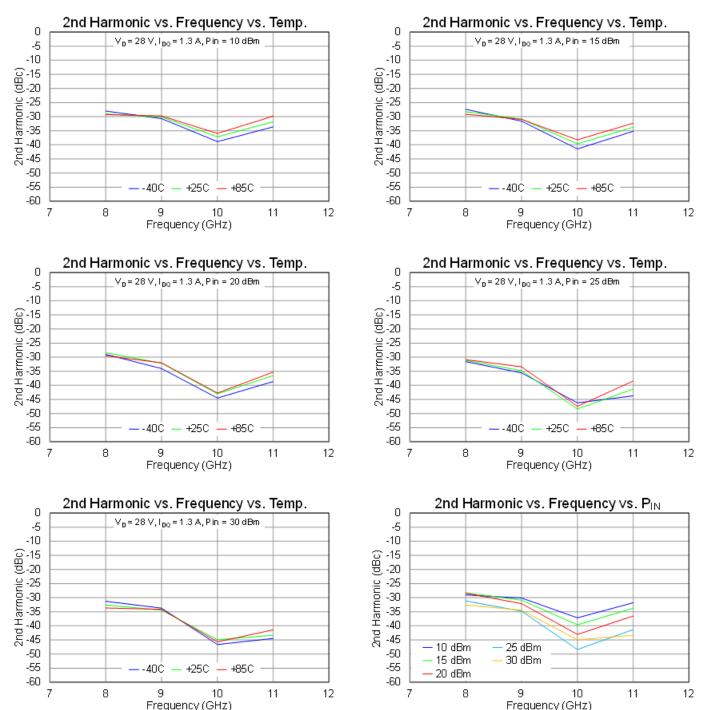
TGM2635-CP X-Band 100 W GaN Power Amplifier

Performance Plots – Large Signal (Pulsed)



TGM2635-CP X-Band 100 W GaN Power Amplifier

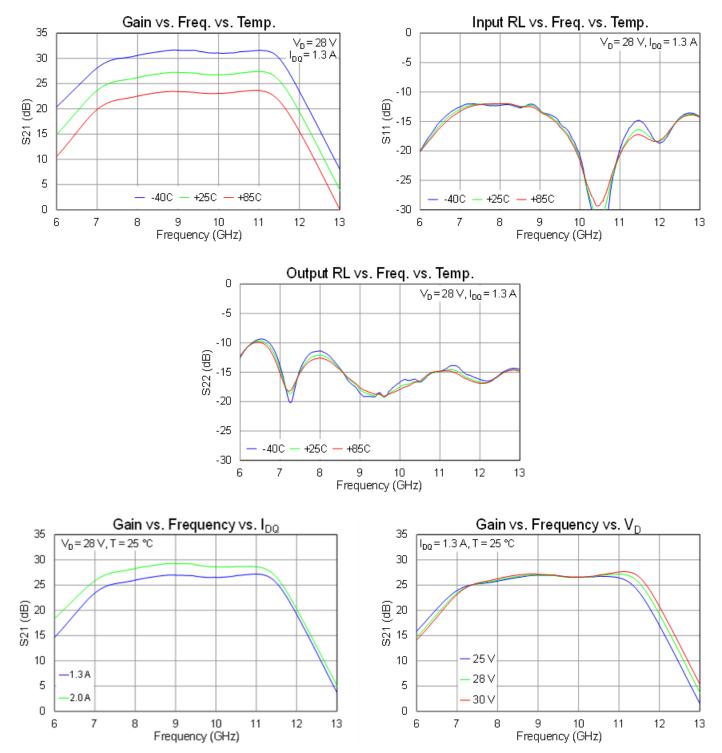
Performance Plots – Large Signal (Pulsed)



TGM2635-CP X-Band 100 W GaN Power Amplifier

Performance Plots – Small Signal (CW)

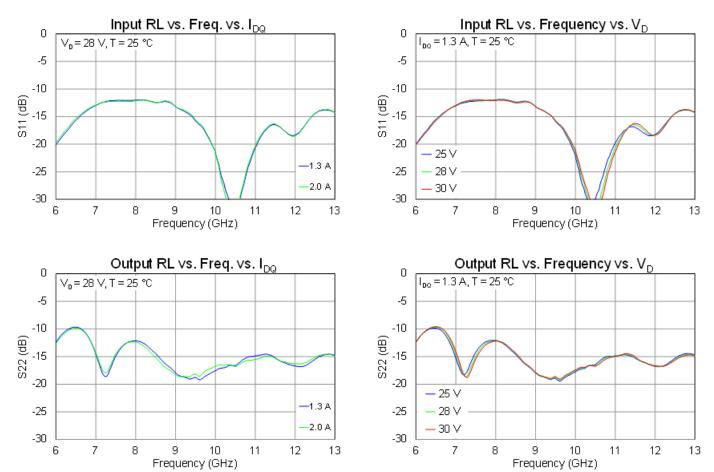
Test conditions unless otherwise noted: 25 °C , V_D = 28 V



TGM2635-CP X-Band 100 W GaN Power Amplifier

Performance Plots – Small Signal (CW)

Test conditions unless otherwise noted: 25 °C , V_{D} = 28 V



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TGM2635-CP X-Band 100 W GaN Power Amplifier

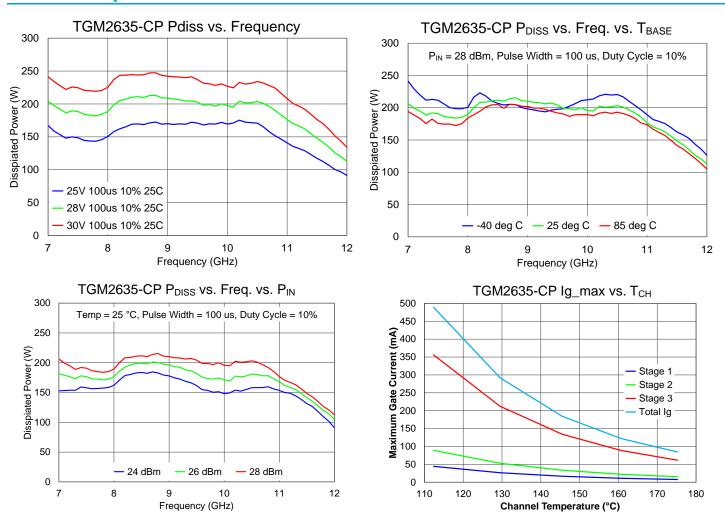
Thermal and Reliability Information

Parameter	Test Conditions	Value	Units
Thermal Resistance (θ _{JC}) ⁽¹⁾	T _{Base} = 85 °C, V _D = 28 V, I _{DQ} = 1.3 A, P _{DISS} = 36.4 W	0.302	°C/W
Channel Temperature, T_{CH} (No RF drive) $^{(2)}$	$T_{Base} = 05$ C, $V_D = 20$ V, $I_{DQ} = 1.3$ A, $P_{DISS} = 30.4$ VV	96.0	°C
Thermal Resistance (θ _{JC}) ⁽¹⁾	$T_{Base} = 85 \text{ °C}, V_D = 28 \text{ V}, I_{DQ} = 1.3 \text{ A}, Freq = 8.7 \text{ GHz}, I_D_Drive = 11.47 \text{ A}, P_{IN} = 28 \text{ dBm}, P_{OUT} = 50.2 \text{ dBm},$	0.226	°C/W
Channel Temperature, T_{CH} (Under RF) ⁽²⁾	$P_{DISS} = 205.4 \text{ W}, PW = 100 \text{ us}, DC = 10\%$	131.5	°C

Notes:

1. Thermal resistance measured at back of package.

2. IR Scan equivalent channel temperature. Refer to the following document: <u>GaN Device Channel Temperature, Thermal</u> <u>Resistance, and Reliability Estimates</u>

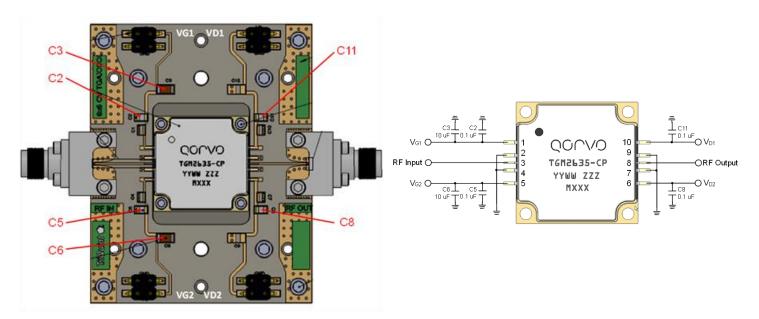


Power Dissipation and Maximum Gate Current

Data Sheet Rev. I, August 2023

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Evaluation Board (EVB) and Application Circuit



Notes:

- 1. See Evaluation Board PCB Information for material and stack up.
- 2. Part requires V_D and V_G biasing from both sides of the EVB.
- 3. EVB is not suitable for long pulse/high duty cycle or CW operation.

Bill of Material

Ref. Des.	Value	Description	Manuf.	Part Number
C3, C6	10 uF, ±20 %, 50 V (1206), X5R	Surface Mount Cap	Various	
C2, C5, C8, C11	0.1 uF, ±10 %, 50 V (0805), X7R	Surface Mount Cap	Various	
J1, J2	2.92 mm	2.92 mm End Launch Connector	Southwest Microwave	1092-02A-5

Bias-Up Procedure

- 2. Set V_{G} to –5.0 V
- 3. Set V_D +28 V
- 4. Adjust V_G more positive until $I_{DQ} = 1.3$ A
- 5. Apply RF signal

Bias-Down Procedure

1. Turn off RF signal
2. Reduce V _G to $-5.0V$. Ensure I _{DQ} ~ 0mA
3. Set V _D to 0V
4. Turn off V _D supply
5. Turn off V _G supply



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Pad Configuration and Description

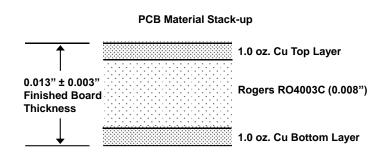


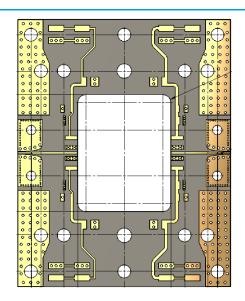
Top View

Pad No.	Label	Description			
1	V _{G1}	Gate voltage stage 1. Bias network is required; see Application Circuit as an example			
2, 4, 7, 9	GND	Ground			
3	RF Input	- Input; matched to 50Ω; DC Blocked			
5	V _{G2}	Gate voltage stage 2. Bias network is required; see Application Circuit as an example			
6	V _{D2}	Drain voltage stage 2. Bias network is required; see Application Circuit as an example.			
8	RF Output	RF Output; matched to 50Ω; DC Blocked, DC Shorted			
10	V _{D1}	Drain voltage stage 1. Bias network is required; see Application Circuit as an example			

Evaluation Board PCB Information

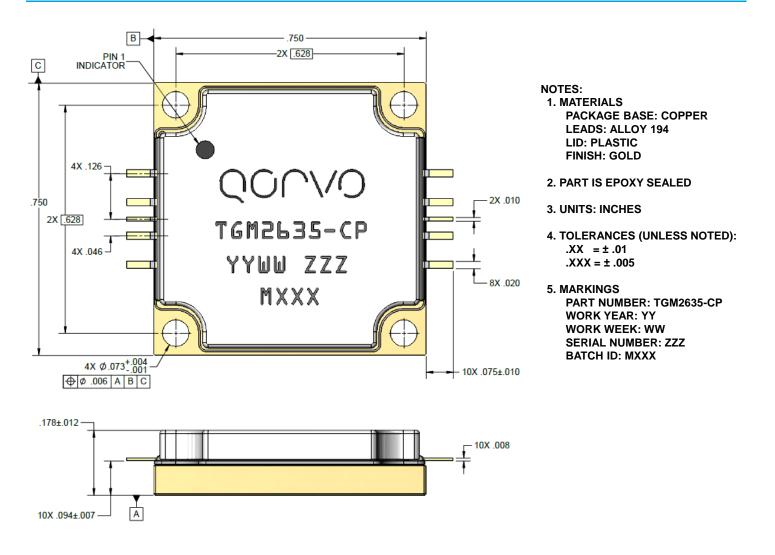
EVB PC Board Layout





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Package Marking and Dimensions





Assembly Notes

- 1. Carefully clean the PC board, base plate, and package leads with alcohol. Allow it to dry fully.
- To improve the thermal and RF performance, Qorvo recommends attaching a heat sink to the bottom
 of the package and apply either a thermal compound (Arctic Silver 5 recommended) or a .004 inch
 (maximum thickness) Indium shim between the heat sink and the package. Refer to the applications
 note <u>Application of Arctic Silver 5 Thermal Compound and Indium Shims for Qorvo CP-style Packaged
 Components</u> for more information.
- 3. The component leads should be manually soldered. Apply a low residue solder alloy meeting J-STD-001 (ROL0, ROL1 or equivalent) with a liquidus temperature below 220 °C to each pin of the TGM2635-CP. The use of low residue/no-clean flux (ROL0, ROL1) is recommended. The package lead temperature should not exceed 260 deg C. Each solder connection should be completed within 2 to 5 seconds. Adding flux during hand soldering of the component leads with localized spot cleaning is acceptable. Soldering irons meeting the requirements of J-STD-001, Appendix A are acceptable.
- 4. The leads should be soldered in a staggered or star pattern from side to side, and never solder two adjacent leads. This allows the heat to dissipate on each lead, and not cause the adjacent leads to become de-soldered and damaged or displaced.



- 5. The packaged part should not be subjected to conventional SMT automated solder reflow processes.
- 6. (The following is for information only. There are many variables in a second level assembly that Qorvo does not control, so Qorvo does not recommend an absolute torque value.) Use screws to attach the component to the heat sink. A suggested final torque value is 16 in-oz. for a 0-80 screw. Start with screws finger tight, then torque to 8 in-oz., then torque to final value. Use the following tightening pattern:





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Handling Precautions

Parameter	Rating	Standard	
ESD-Human Body Model (HBM)	Class 0B	ANSI / ESDA / JEDEC JS-001	Caution!
ESD-Charged Device Model (CDM)	Class C3	ANSI / ESDA / JEDEC JS-002	ESD-Sensitive Device
MSL-Moisture Sensitivity Level	N/A		

Solderability

The component leads should be manually soldered, and the package cannot be subjected to conventional reflow processes. The use of no-clean solder to avoid washing after soldering is recommended.

RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C15H12Br402) Free
- PFOS Free
- SVHC Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

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